

High Voltage Power Transistor Isolated Package Applications MJF47G

Designed for line operated audio output amplifiers, switching power supply drivers and other switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

Features

- Electrically Similar to the Popular TIP47
- 250 V_{CEO(sus)}
- 1 A Rated Collector Current
- No Isolating Washers Required
- Reduced System Cost
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation
- This is a Pb-Free Device*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CB}	350	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
RMS Isolation Voltage (Note 1) Test No. 1 Per Figure 10 Test No. 2 Per Figure 11 Test No. 3 Per Figure 12 (for 1 sec, R.H. < 30%, T _A = 25°C)	V _{ISOL}	4500 3500 1500	V
Collector Current - Continuous - Peak	I _C	1 2	Adc
Base Current - Continuous	Ι _Β	0.6	Adc
Total Power Dissipation (Note 2) @ T _C = 25°C Derate above 25°C	P _D	28.4 0.227	W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

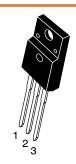
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	4.4	°C/W
Lead Temperature for Soldering Purposes	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Proper strike and creepage distance must be provided.
- Measurement made with thermocouple contacting the bottom insulated surface (in a location beneath the die), the devices mounted on a heatsink with thermal grease and a mounting torque of ≥ 6 in. lbs.
- *For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

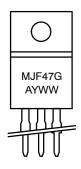
1

NPN SILICON POWER TRANSISTOR 1 AMPERE 250 VOLTS, 28 WATTS



TO-220 FULLPACK CASE 221D STYLE 2

MARKING DIAGRAM



G = Pb-Free PackageA = Assembly LocationY = Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MJF47G	TO-220 FULLPACK (Pb-Free)	50 Units/Rail

MJF47G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•	•		
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	250	-	Vdc
Collector Cutoff Current (V _{CE} = 150 Vdc, I _B = 0)	I _{CEO}	_	0.2	mAdc
Collector Cutoff Current (V _{CE} = 350 Vdc, V _{BE} = 0)	I _{CES}	-	0.1	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	1	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I _C = 0.3 Adc, V _{CE} = 10 Vdc) (I _C = 1 Adc, V _{CE} = 10 Vdc)	h _{FE}	30 10	150 -	-
Collector–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1	Vdc
Base-Emitter On Voltage (I _C = 1 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	<u>.</u>			
Current Gain – Bandwidth Product (I _C = 0.2 Adc, V _{CE} 10 Vdc, f = 2 MHz)	f _T	10	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

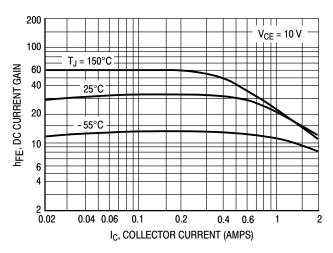


Figure 1. DC Current Gain

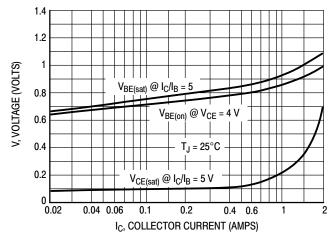


Figure 2. "On" Voltages

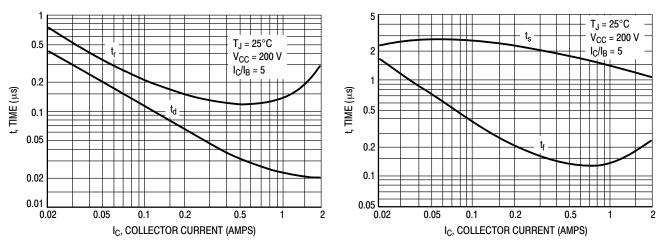


Figure 3. Turn-On Time

Figure 4. Turn-Off Time

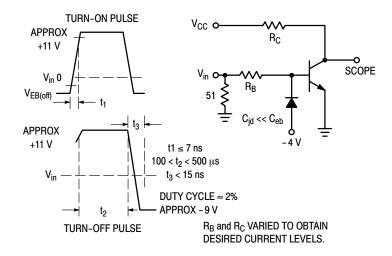


Figure 5. Switching Time Equivalent Circuit

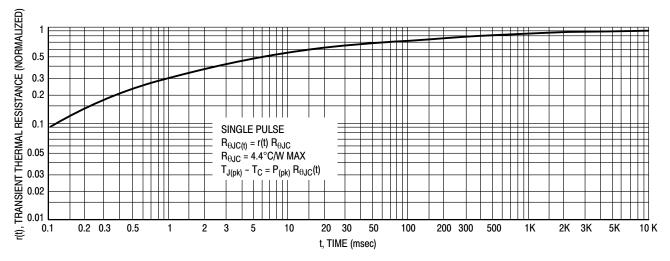


Figure 6. Thermal Response

MJF47G

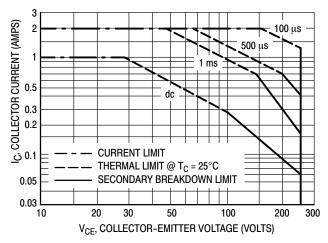


Figure 7. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

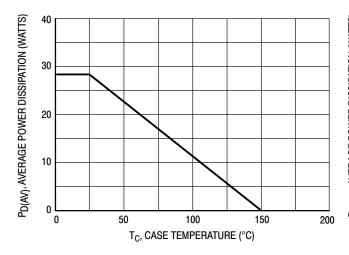


Figure 8. Power Derating

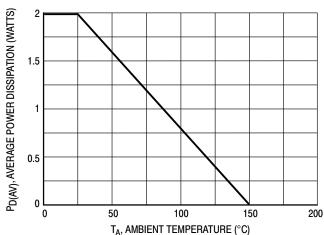


Figure 9. Power Derating

MJF47G

TEST CONDITIONS FOR ISOLATION TESTS*

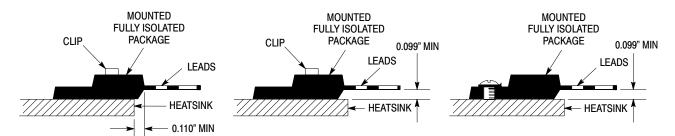


Figure 10. Clip Mounting Position for Isolation Test Number 1

Figure 11. Clip Mounting Position for Isolation Test Number 2

Figure 12. Screw Mounting Position for Isolation Test Number 3

MOUNTING INFORMATION

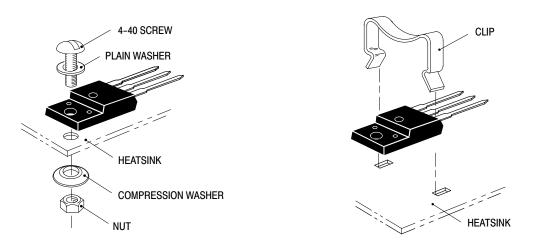


Figure 13. Typical Mounting Techniques*

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, **onsemi** does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

^{*}Measurement made between leads and heatsink with all leads shorted together

^{**}For more information about mounting power semiconductors see Application Note AN1040.





SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

0

AYWW

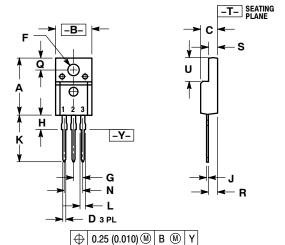
xxxxxxG

AKA

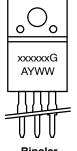
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

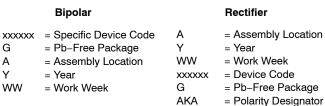
	INCHES MILLIMETE		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
С	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS



STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER CATHODE
 ANODE 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE 3. CATHODE





DOCUMENT NUMBER:	98ASB42514B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-220 FULLPAK		PAGE 1 OF 1	

Υ

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales